

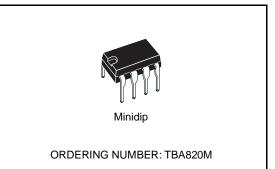
TBA820M

1.2W AUDIO AMPLIFIER

DESCRIPTION

The TBA820M is a monolithic integrated audio amplifier in a 8 lead dual in-line plastic package. It is intended for use as low frequency class B power amplifier with wide range of supply voltage: 3 to 16V, in portable radios, cassette recorders and players etc. Main features are: minimum working supply voltage of 3V, low quiescent current, low number of external components, good ripple rejection, no cross-over distortion, low power dissipation.

Output power: P_o = 2W at 12V/8 Ω , 1.6W at 9V/4 Ω and 1.2W at 9V/8 $\Omega.$



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply voltage	16	V
lo	Output peak current	1.5	А
P _{tot}	Power dissipation at $T_{amb} = 50^{\circ}C$	1	W
T _{stg} , T _j	Storage and junction temperature	-40 to 150	°C

TEST AND APPLICATION CIRCUITS

Figure 1. Circuit diagram with load connected to the supply voltage

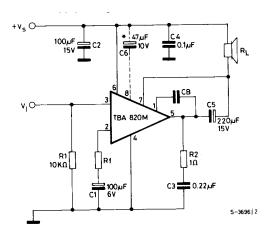
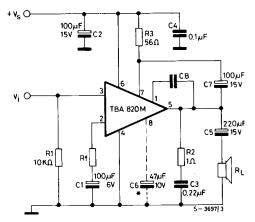


Figure 2. Circuit diagram with load connected to ground

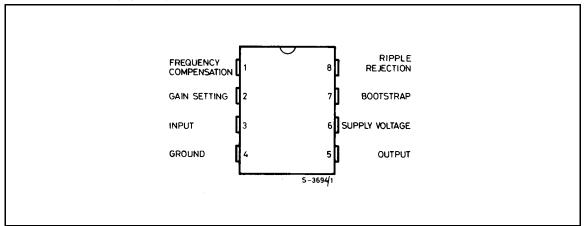


* Capacitor C6 must be used when high ripple rejection is requested.

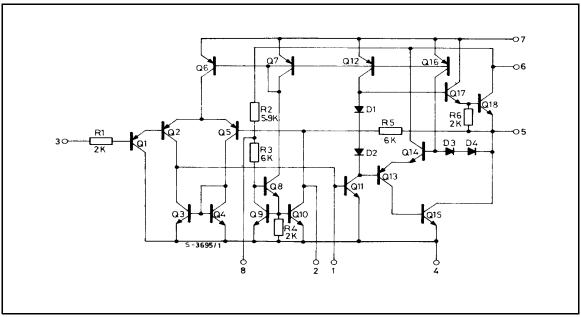
September 2003

TBA820M

PIN CONNECTION (top view)



SCHEMATIC DIAGRAM



THERMAL DATA

Symbol	Parameter	Value	Unit
R _{th-j-amb}	Thermal resistance junction-ambient max	100	°C/W

57

2/6

Symbol	Parameter	Test conditions Min. Typ. Max.			Unit			
Vs	Supply voltage			3		16	V	
Vo	Quiescent output voltage (pin 5)			4	4.5	5	V	
l _d	Quiescent drain current				4	12	mA	
Ib	Bias current (pin 3)				0.1		μA	
Po	Output power		$f = 1 \text{ kHz}$ $R_L = 8\Omega$ $R_L = 4\Omega$ $R_L = 8\Omega$ $R_L = 4\Omega$ $R_L = 4\Omega$	0.9	2 1.6 1.2 0.75 0.25		W W W W	
Ri	Input resistance (pin 3)	f = 1 kHz			5		MΩ	
В	Frequency response (-3 dB)	$R_L = 8\Omega$			25 to 7,000			
		$\begin{array}{l} C_5 = 1000 \; \mu F \\ R_f = 120 \Omega \end{array}$	C _B = 220 pF	25 to 20,000		Hz		
d	Distortion	$P_0 = 500 \text{ mW}$	$R_f = 33\Omega$		0.8			
		$\begin{array}{c} R_{L} = 8\Omega \\ f = 1 \text{ kHz} \\ \end{array} \qquad \qquad R_{f} = 120\Omega \end{array}$		0.4		%		
Gv	Voltage gain (open loop)	f = 1 kHz	$R_L = 8\Omega$		75		dB	
Gv	Voltage gain (closed loop)	$R_L = 8\Omega$	$R_f = 33\Omega$		45	dB		
		f = 1 kHz	R _f = 120Ω		34		dB	
e _N	Input noise voltage (*)				3		μV	
i _N	Input noise current (*)				0.4		nA	
S+N	Signal to noise ratio (*)	$P_0 = 1.2W$	R1 = 10KΩ		80		40	
N		$\begin{array}{l} R_L = 8\Omega \\ G_v = 34 \; dB \end{array}$	R1 = 50 kΩ		70		dB	
SVR	Supply voltage rejection (test circuit of fig. 2)	$\begin{array}{c} R_{L} = 8\Omega \\ f_{(\text{ripple})} = 100 \; \text{Hz} \\ C6 = 47 \; \mu\text{F} \\ R_{f} = 120\Omega \end{array}$			42		dB	

ELECTRICAL CHARACTERISTICS (Refer to the test circuits Vs = 9V, T_{amb} = 25 °C unless otherwise specified)

(*) B = 22 Hz to 22 KHz

57

Figure 3. Output power vs. supply voltage

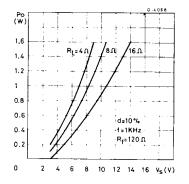


Figure 4. Harmonic distortion vs. output power

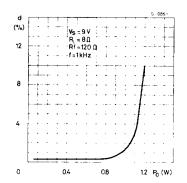


Figure 5. Power dissipation and efficiency vs. output power

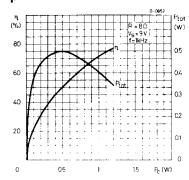


Figure 6. Maximum power dissipation (sine wave operation)

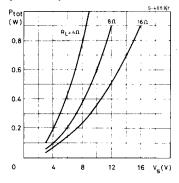


Figure 7. Suggested value of $C_B vs. R_f$

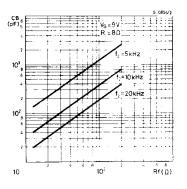


Figure 8. Frequency response

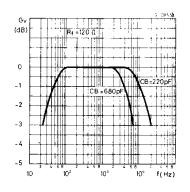
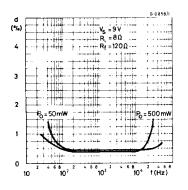
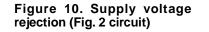


Figure 9. Harmonic distortion vs. frequency





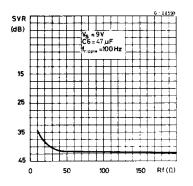
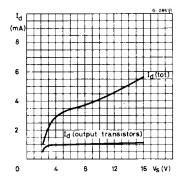


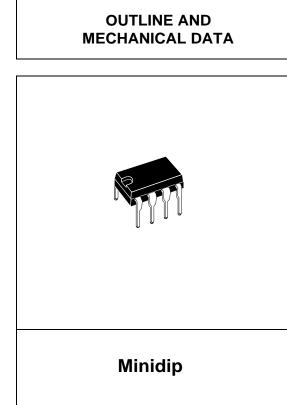
Figure 11. Quiescent current vs. supply voltage

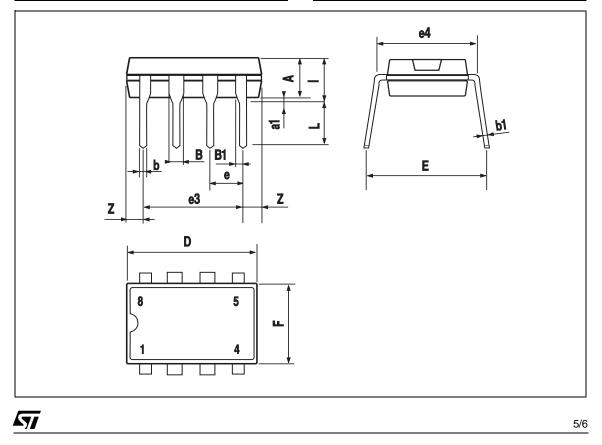


57

4/6

						1	
		inch			mm		DIM.
OU MECH	MAX.	TYP.	MIN.	MAX.	TYP.	MIN.	DINI.
		0.131			3.32		А
			0.020			0.51	a1
	0.065		0.045	1.65		1.15	В
	0.022		0.014	0.55		0.356	b
	0.012		0.008	0.304		0.204	b1
R.	0.430			10.92			D
	0.384		0.313	9.75		7.95	Е
ų		0.100			2.54		е
		0.300			7.62		e3
		0.300			7.62		e4
	0.260			6.6			F
	0.200			5.08			Ι
Mi	0.150		0.125	3.81		3.18	L
	0.060			1.52			Z





Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners

© 2003 STMicroelectronics - All rights reserved

STMicroelectronics GROUP OF COMPANIES

Australia – Belgium - Brazil - Canada - China – Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States

www.st.com

6/6

57